



Silicon Controlled Rectifiers

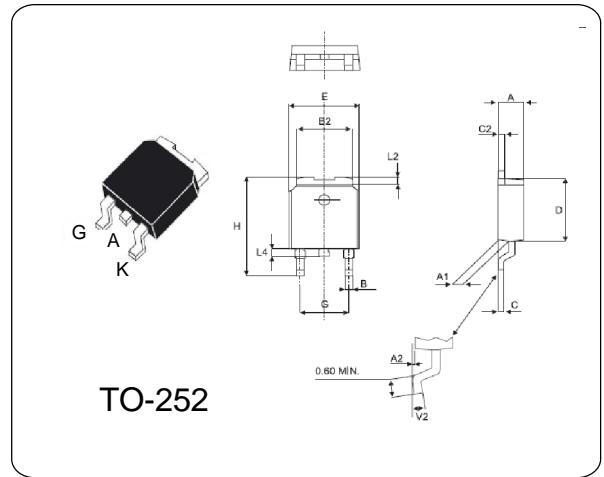
MCR708A

DESCRIPTION

PNPN devices designed for high volume, low cost consumer applications such as temperature, light and speed control; process and remote control; and warning systems where reliability of operation is critical.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Parameter	Symbol	Typ	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}	600	V
Average on-state current	$I_{T(AV)}$	2.6	A
RMS on-state current	$I_{T(RMS)}$	4.0	A
Non-repetitive peak on-state current	I_{TSM}	25	A
Max. Operating Junction Temperature	T_j	110	°C
Storage Temperature	T_{stg}	-45~150	°C



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Repetitive peak off-state voltages	V_{DRM} V_{RRM}		600	—	—	V
Average on-state current	$I_{T(AV)}$	half sine wave; $T_{mb} < 103\text{ °C}$	—	2.6	—	A
RMS on-state current	$I_{T(RMS)}$	all conduction angles	—	4.0	—	A
On-state voltage	V_{TM}	$I_{TM}=8.2A, t_p=380\ \mu s$	—	—	2.2	V
Holding current	I_H	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	—	—	5.0	mA
Latching current	I_L	$V_D = 12\text{ V}; I_{GT} = 0.1\text{ A}$	—	—	8.0	mA
Gate trigger current	I_{GT}	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	10	—	75	uA
Gate trigger voltage	V_{GT}	$V_D = 12\text{ V}; I_T = 0.1\text{ A}$	—	—	1.0	V